

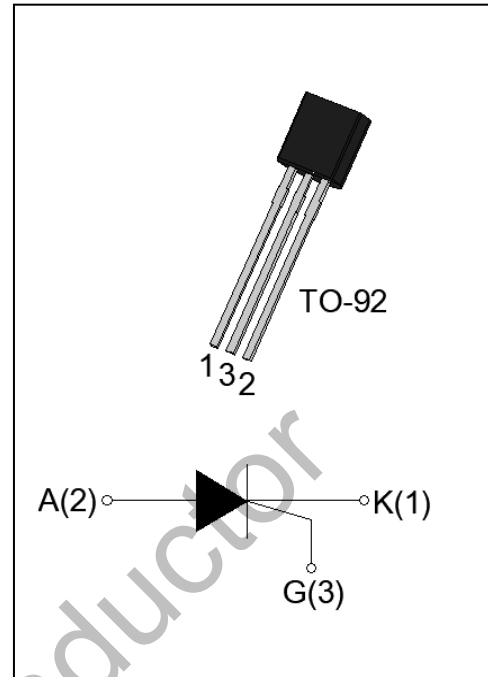
BT169D 0.8A Sensitive SCR

DESCRIPTION:

The BT169D SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package TO-92 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	≤ 200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125 ^①	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 60^{\circ}C$)	$I_{T(AV)}$	0.5	A
RMS on-state current ($T_c \leq 60^{\circ}C$)	$I_{T(RMS)}$	0.8	A
Non repetitive surge peak on-state current ($t_p=10ms$, $T_j=25^{\circ}C$)	I_{TSM}	8	A
Non repetitive surge peak on-state current ($t_p=8.3ms$, $T_j=25^{\circ}C$)		9	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	0.32	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^{\circ}C$)	I_{GM}	1	A

Average gate power dissipation ($T_j=125^{\circ}\text{C}$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV

NOTE 1: When we parallel connect a $\leq 1\text{K}\Omega$ resistor between Gate and Cathode, the T_j can reach 125°C ; if without this resistor, the T_j only can reach 110°C .

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	4	mA
I_H	$I_T=0.05\text{A}$	-	-	3	mA
dV/dt	$V_D=540\text{V } T_j=125^{\circ}\text{C } R_{GK}=1\text{K}\Omega$	200	-	-	V/ μs
	$V_D=540\text{V } T_j=125^{\circ}\text{C } R_{GK}=220\Omega$	500	-	-	
t_{on}	$I_G=10\text{mA } I_A=20\text{mA } I_R=2\text{mA}$	-	2	-	μs
t_{off}	$T_j=25^{\circ}\text{C}$	-	50	-	μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_T=1\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.35	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.93	V
R_D	Dynamic Resistance	$T_j=125^{\circ}\text{C}$	0.34	Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	2	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	63	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient (DC)	140	$^{\circ}\text{C/W}$

FIG.1: Maximum power dissipation versus RMS on-state current

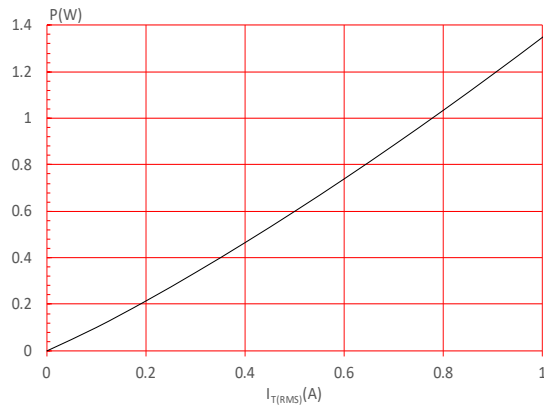


FIG.2: RMS on-state current versus case temperature

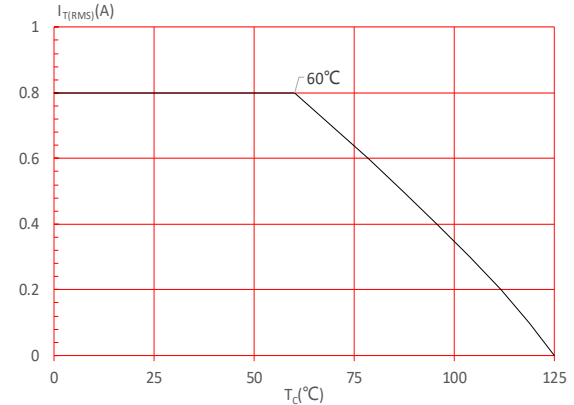


FIG.3: Surge peak on-state current versus number of cycles

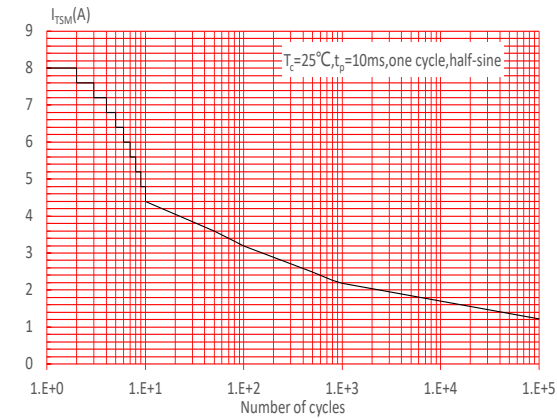


FIG.4: On-state characteristics

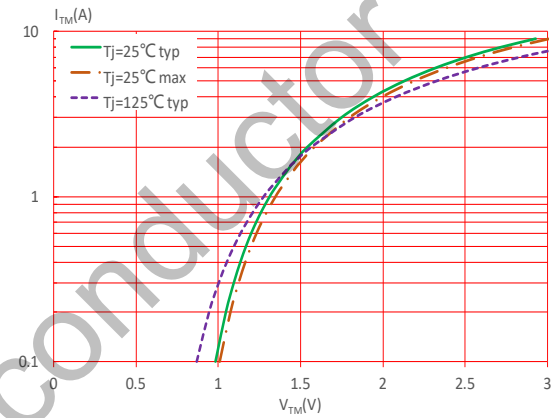


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

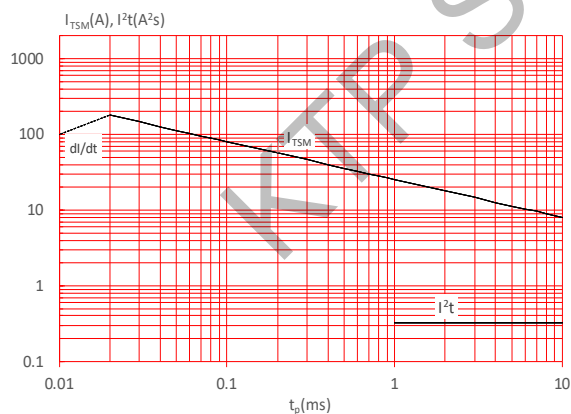


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

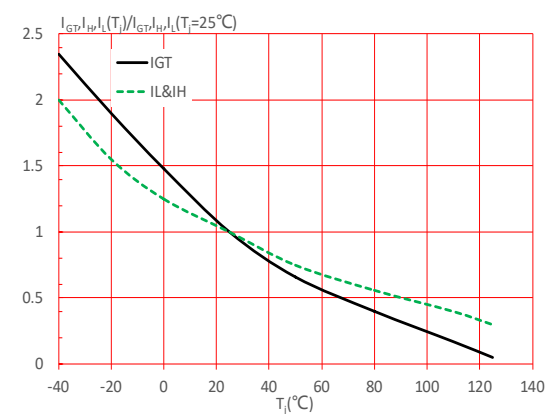
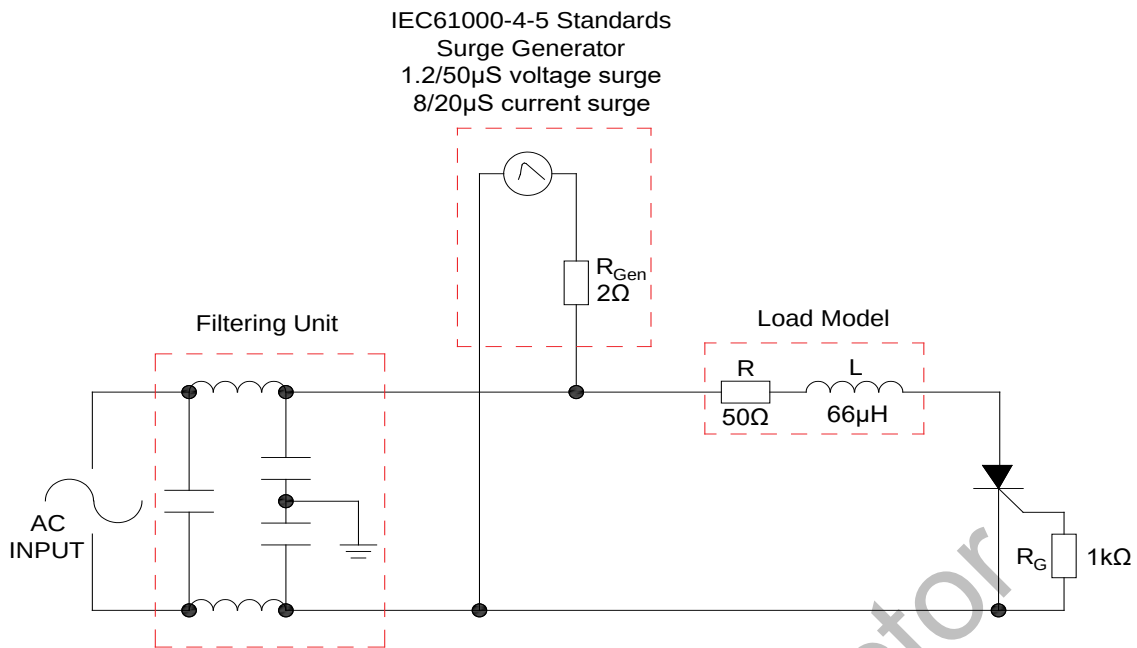
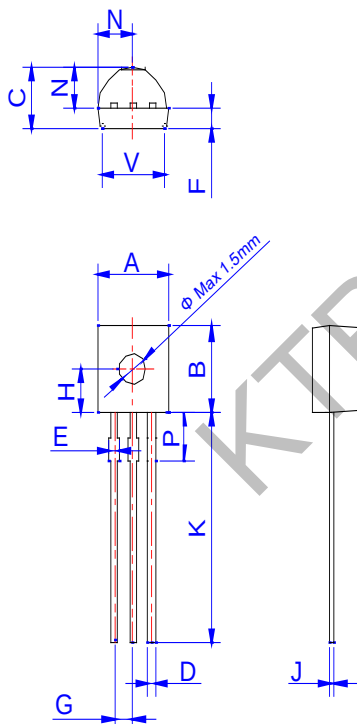


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	1.10		1.30			0.051
G	1.10		1.40	0.043		0.055
H	2.20		2.40	0.087		0.094
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.80		2.30	0.071		0.091
V	4.10		4.50	0.161		0.177